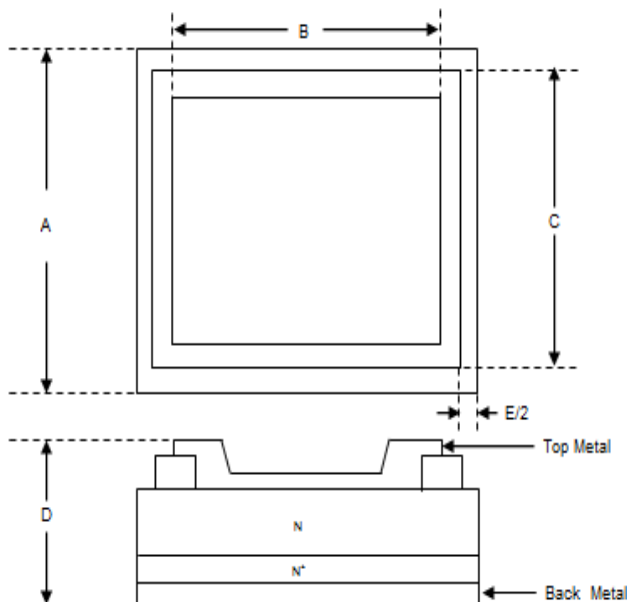


### Trench Schottky Barrier Diode Wafer (TSBD)



Item	Dimensions	
	um	mil
Die Size (A)	3080	120
Top Metal Pad Size (B)	2972	117.0
Passivation Seal (C)	3010	118.5
Wafer Thickness (D)	260	10.2
Scribe Line Width (E)	70	2.76
Other Informations		
Wafer Size	6"	
Gross Die	1600	
Top Metal	Al	
Back Metal	Ag	

Electrical Characteristics @TA=25 °C				
Item	Symbol	Spec. Limit	Die Sort	Unit
Maximum Repetitive Peak Reverse Voltage @0.3mA	$V_{RRM}$	100	105	V
Maximum Average Forward Rectified Current	$I_o$	20	-	A
Forward Voltage Drop, @ $I_F=3A$ @ $I_F=15A$ @ $I_F=20A$	$V_F$	- 0.64 0.72	0.47 - -	V
Maximum Reverse Current at Rated $V_{RRM}$	$I_R$	90	50	$\mu A$
Peak Forward Surge Current, 8.3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC Method)	$I_{FSM}$	320	-	A
Operating Temperature Range	$T_J$	-50 to +150	-	°C
Storage Temperature Range	$T_{STG}$	-50 to +150	-	°C